Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-9. (Canceled)

Claim 10. (New) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate; and

a second wiring line formed over the first wiring line with an insulating film interposed therebetween,

wherein the first wiring line and the second wiring line extend in parallel with each other, and

wherein the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 11. (New) An integrated circuit using a thin film transistor according to claim 10, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 12. (New) An integrated circuit using a thin film transistor according to claim 10, wherein the insulating film comprises silicon nitride.

Claim 13. (New) An integrated circuit using a thin film transistor according to claim 10, wherein the insulating film comprises an interlayer insulating film.

Claim 14. (New) An integrated circuit using a thin film transistor according to claim 10, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 15. (New) An integrated circuit using a thin film transistor according to claim 10, wherein the second wiring comprises aluminum.

Claim 16. (New) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate; and

a second wiring line formed over the first wiring line with an insulating film interposed therebetween,

wherein the first wiring line is formed on a same layer as a gate electrode of the thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other, and

wherein the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 17. (New) An integrated circuit using a thin film transistor according to claim 16, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 18. (New) An integrated circuit using a thin film transistor according to claim 16, wherein the insulating film comprises silicon nitride.

Claim 19. (New) An integrated circuit using a thin film transistor according to claim 16, wherein the insulating film comprises an interlayer insulating film.

Claim 20. (New) An integrated circuit using a thin film transistor according to claim 16, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 21. (New) An integrated circuit using a thin film transistor according to claim 16, wherein the second wiring comprises aluminum.

Claim 22. (New) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate; and

a second wiring line formed over the first wiring line with an insulating film interposed therebetween,

wherein the second wiring line is formed on a same layer as a source or a drain electrode of the thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other, and

wherein the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 23. (New) An integrated circuit using a thin film transistor according to claim 22, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 24. (New) An integrated circuit using a thin film transistor according to claim 22, wherein the insulating film comprises silicon nitride.

Claim 25. (New) An integrated circuit using a thin film transistor according to claim 22, wherein the insulating film comprises an interlayer insulating film.

Claim 26. (New) An integrated circuit using a thin film transistor according to claim 22, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 27. (New) An integrated circuit using a thin film transistor according to claim 22, wherein the second wiring comprises aluminum.

Claim 28. (New) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate; and

a second wiring line formed over the first wiring line with an insulating film interposed therebetween,

wherein the first wiring line is formed on a same layer as a gate electrode of the thin film transistor,

wherein a width of the first wiring is smaller than that of the second wiring,

wherein the first wiring line and the second wiring line extend in parallel with each other, and

wherein the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 29. (New) An integrated circuit using a thin film transistor according to claim 28, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 30. (New) An integrated circuit using a thin film transistor according to claim 28, wherein the insulating film comprises silicon nitride.

Claim 31. (New) An integrated circuit using a thin film transistor according to claim 28, wherein the insulating film comprises an interlayer insulating film.

Claim 32. (New) An integrated circuit using a thin film transistor according to claim 28, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 33. (New) An integrated circuit using a thin film transistor according to claim 28, wherein the second wiring comprises aluminum.

Claim 34. (New) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate; and

a second wiring line formed over the first wiring line with an insulating film interposed therebetween,

wherein the second wiring is formed on a same layer as a source or a drain electrode of the thin film transistor,

wherein a width of the first wiring is smaller than that of the second wiring,

wherein the first wiring line and the second wiring line extend in parallel with each other, and

wherein the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 35. (New) An integrated circuit using a thin film transistor according to claim 34, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 36. (New) An integrated circuit using a thin film transistor according to claim 34, wherein the insulating film comprises silicon nitride.

Claim 37. (New) An integrated circuit using a thin film transistor according to claim 34, wherein the insulating film comprises an interlayer insulating film.

Claim 38. (New) An integrated circuit using a thin film transistor according to claim 34, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 39. (New) An integrated circuit using a thin film transistor according to claim 34, wherein the second wiring comprises aluminum.